

🐡 Introduction of Nano Science and Tech 🐲



Quantum Effects in Nanostructures -Confinement and Coherence

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Course Website: nanoHUB.org Compass.illinois.edu

ME 498

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Departure from continuum

- Quantum Effects (Two Lectures)
 - Atomic bonding
 - Confinement
 - Coherence
- **Basics of Kinetics and Statistical Thermodynamics (Two Lectures)**
 - Microscopic Origin of Macroscopic Laws
 - Transport properties

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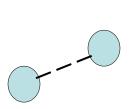
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Quantum Effects



How the energy are presented in discrete levels?



$$E_{translation} = \frac{\hbar^2 k^2}{2m}$$

$$E_{\text{Vibration}} = h\nu(n + \frac{1}{2}); \nu = \frac{1}{2\pi} \sqrt{\frac{K}{m}}$$
$$(n=0,1,2\cdots)$$

$$E_{\rm Rotation}\!=\!\!hBl(l+1)\ (l\!=\!0,1\cdots)$$

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Solution of a Confined 1D system



• From the above boundary conditions, we obtain:

$$\sin(kD) = 0;$$

$$k_n D = n\pi$$

(n=0, \pm 1, \pm 2, ...) the probability of the particles can only take standing wave forms!

Recall:

$$k = \frac{\sqrt{2mE}}{\hbar}$$

Finite Energy

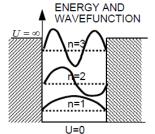
steps:

$$E_n = \frac{n^2 \hbar^2 \pi^2}{2mD^2}$$

When D=1nm, m_e=9.1x10⁻³¹kg

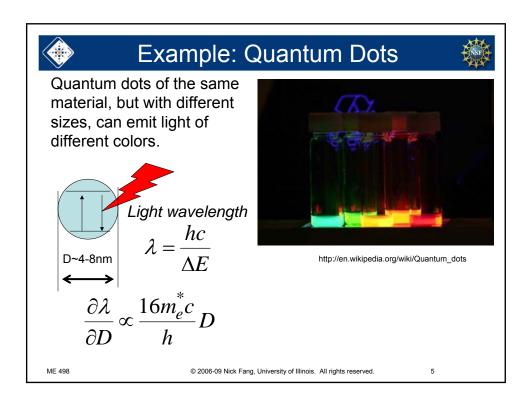
 $E_2-E_1=1.13eV!$

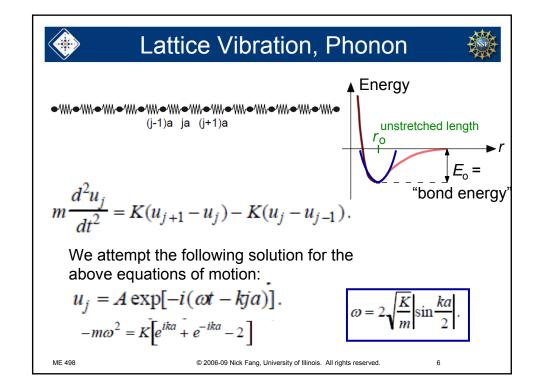


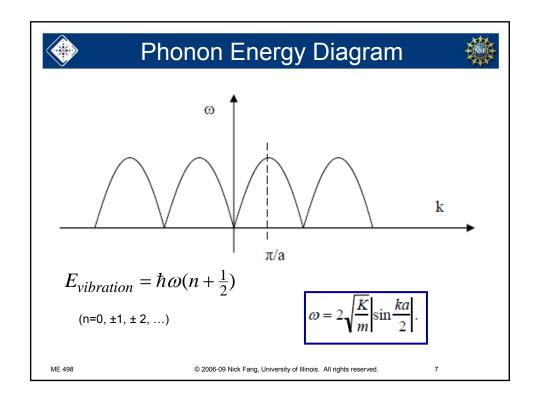


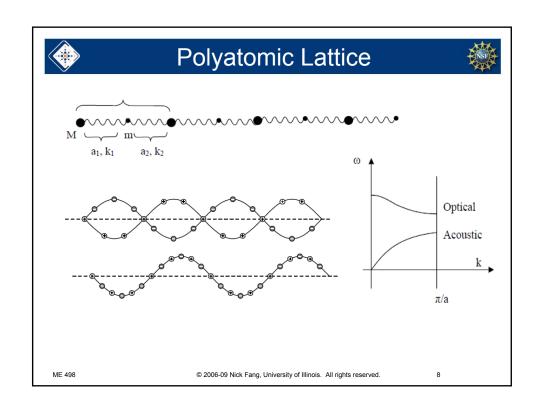
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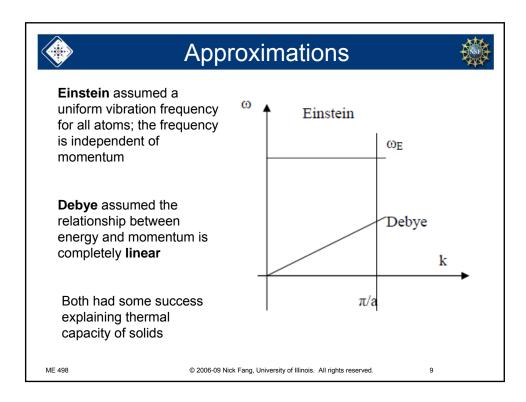
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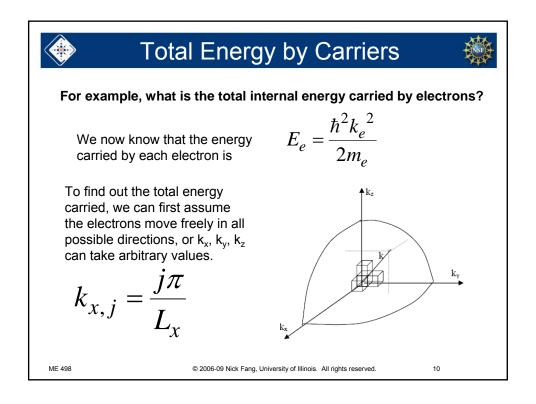














Density of States (DOS)



For math convenience, we introduce a measure of the number of available quantum mechanical states per unit volume. This is typically measured at a specified energy E or momentum k.

E.G. the number of states within k and k+dk is

$$D(k)dk = \frac{4\pi k^2 dk}{V}$$

Convert this to the number of states within E and E+dE:

$$D(E)dE = \left(\frac{4\pi k^2}{V}\right) \left(\frac{dk}{dE}\right) dE$$

$$k = \frac{\sqrt{2mE}}{\hbar} \quad \frac{dk}{dE} = \frac{\sqrt{m/2E}}{\hbar}$$

For bulk material we obtain:

$$D(E)dE = \frac{1}{V} \left(\frac{\sqrt{2m}}{\hbar}\right)^3 \left(\sqrt{E}\right) dE$$

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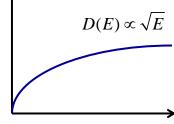
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Electron Density of States (Bulk)







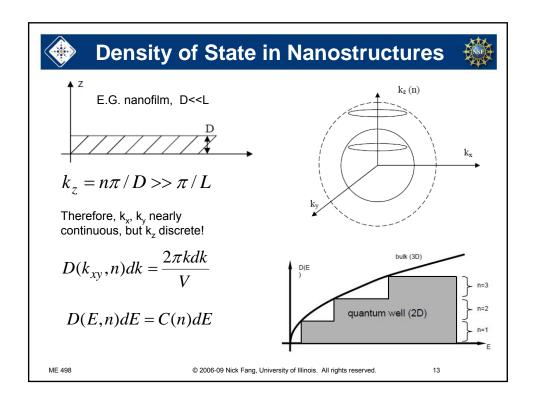
Importance:

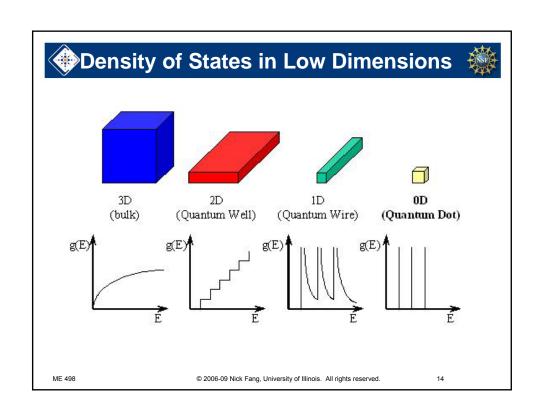
Knowing the density of states allows us to find out the total internal energy, heat capacity, etc

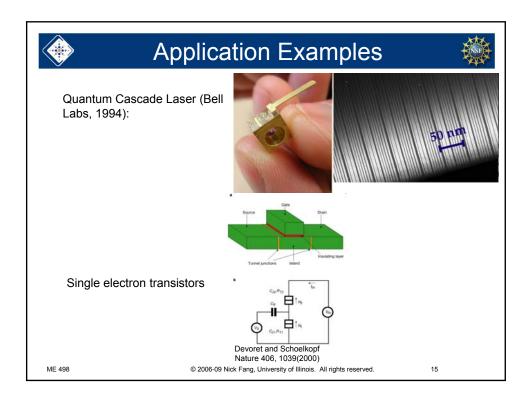
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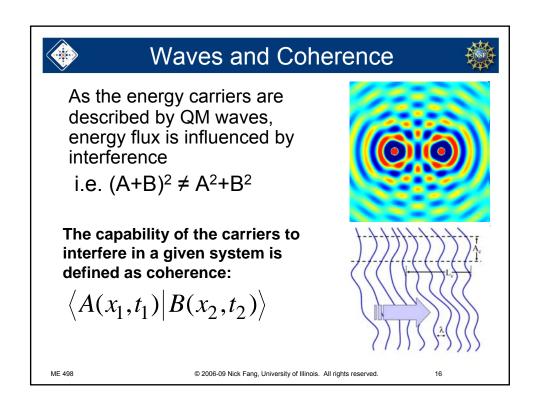
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Size Effect



E.G. Reflection of light on a thin film

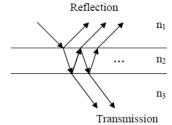
$$r = \frac{E_r}{E_i} = \frac{r_{12} + r_{23} \exp[2i\varphi_2]}{1 + r_{12}r_{23} \exp[2i\varphi_2]}$$

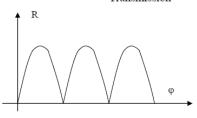
$$\varphi = k_z d$$

Note: R is maximized when

$$d = \pi/k_z(E)$$

For 0.5eV electron, this is about 1.2nm 0.5eV photon, this is ~ 120nm

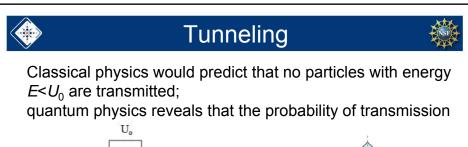


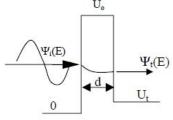


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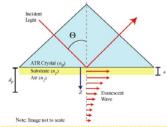
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In optics, it is called evanescent waves:



 $E_z(x, y, z) = E_0 \exp(ik_x x + ik_y y - \gamma z)$

 $\gamma = \sqrt{k_x^2 + k_y^2 - \left(\frac{2\pi n_3}{\lambda}\right)^2}$

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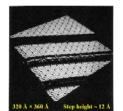
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Applications of Tunneling



E.G. Scanning Tunneling Microscope (STM) invented by G. Binnig and H. Rohrer in 1982 (Nobel Prize in Physics, 1986)



Atomic image of silicon single crystal

E.G. Attenuated Total Internal Reflection (ATR) Sensor (commercial products such as GE BiaCORE provide ppm sensitivity)



http://www.sensorsportal.com/HTML/DIGEST/december_02/MicroSpec_Sensor.jpg

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Additional Reading



- Tien, Majumdar, Gerner, "Microscale Energy Transport", Chapter 1, Taylor&Francis (pdf online)
- Introduction to Scanning Tunneling Microscopy on nanoHUB:

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